



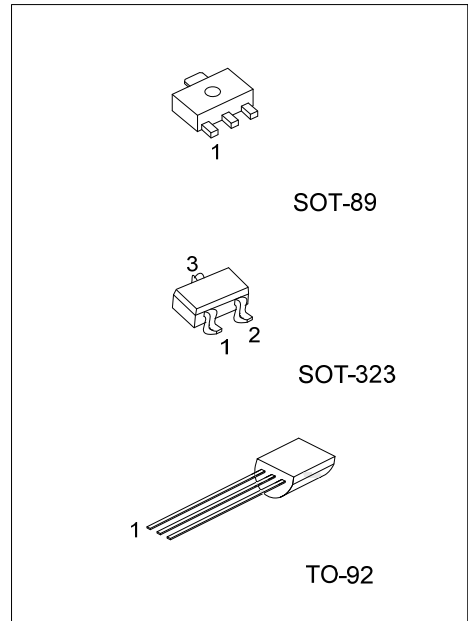
2SC3355

NPN SILICON EPITAXIAL TRANSISTOR

HIGH FREQUENCY LOW
NOISE AMPLIFIER
NPN SILICON EPITAXIAL
TRANSISTOR

FEATURES

- * Low Noise and High Gain
- * High Power Gain



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC3355L-AB3-R	2SC3355G-AB3-R	SOT-89	B	C	E	Tape Reel
2SC3355L-AL3-R	2SC3355G-AL3-R	SOT-323	B	E	C	Tape Reel
2SC3355L-T92-B	2SC3355G-T92-B	TO-92	B	E	C	Tape Box
2SC3355L-T92-K	2SC3355G-T92-K	TO-92	B	E	C	Bulk

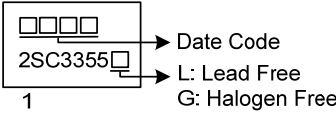
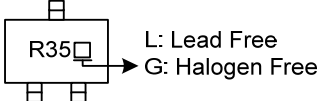
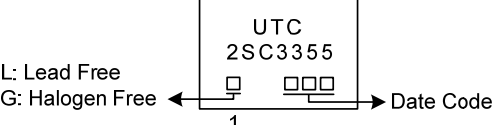
Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SC3355G-AB3-R</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) R: Tape Reel, B: Tape Box, K: Bulk</p> <p>(2) AB3: SOT-89, AL3: SOT-323, T92: TO-92</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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2SC3355

NPN SILICON EPITAXIAL TRANSISTOR

MARKING

Package	MARKING
SOT-89	 <p> Date Code L: Lead Free G: Halogen Free 1 </p>
SOT-323	 <p> L: Lead Free G: Halogen Free </p>
TO-92	 <p> UTC 2SC3355 L: Lead Free G: Halogen Free Date Code 1 </p>

■ ABSOLUTE MAXIMUM RATING ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-base voltage		V_{CBO}	20	V
Collector-emitter voltage		V_{CEO}	12	V
Emitter-base voltage		V_{EBO}	3	V
Collector current		I_C	100	mA
Power dissipation	SOT-89	P_D	500	mW
	SOT-323		200	mW
	TO-92		600	mW
Junction Temperature		T_J	+125	$^{\circ}\text{C}$
Operating Temperature		T_{OPR}	-20 ~ +85	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-40 ~ +150	$^{\circ}\text{C}$

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I_{CBO}	$V_{CB}=10\text{V}, I_E=0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=1\text{V}, I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=10\text{V}, I_C=20\text{mA}$	50		300	
Gain bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}$		7		GHz
Feed-Back Capacitance	C_{re}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$			1.0	pF
Noise Figure	NF	$V_{CE}=10\text{V}, I_C=7\text{mA}, f=1.0\text{GHz}$		1.1		dB

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